

In th Sp cification

Amend the title as follows:

~~Circuitry Comprising Roughened Platinum Layers, Platinum-Containing Materials, Capacitors Comprising Roughened Platinum Layers, Methods Of Forming Roughened Layers Of Platinum, And Methods Of Forming Capacitors~~ Platinum-Containing Integrated Circuits And Capacitor Constructions

At page 1, before the "Technical Field" section, please insert:

RELATED PATENT DATA

This patent resulted from a continuation of U.S. Patent Application Serial No. 09/421,625, which was filed on October 19, 1999; which is a continuation of U.S. Patent Application Serial No. 09/281,735, which was filed March 30, 1999, now U.S. Patent No. 5,990,559; which is a divisional of U.S. Patent Application Serial No. 09/141,840, which was filed August 27, 1998 and is now U.S. Patent No. 6,583,022.

At page 10, replace the paragraph starting at line 5 with the following:

A fragmentary top view of wafer fragment 10 is shown in Fig. 2. Layer 18 is preferably a continuous layer (defined as a layer without cavities extending therethrough to an underlying layer -- such as the underlying layer 16 of Fig. 2) across its entirety. Alternatively, some portion of layer 18 is continuous. For example, consider an application where layer 18 overlies and contacts a conductive layer to form a circuit device comprising both layer 18 and the underlying conductive layer. In such applications, it is generally still desired that a substantial portion of layer 18 be continuous to, for example, maintain a uniform electrical contact between layer 18 and the underlying conductive layer. Such substantial portion will preferably cover a surface area of at least about 4×10^6 square Angstroms. A surface area of about 4×10^6 square Angstroms is illustrated in Fig. 3 2 as a square 50 having sides of about 2000 Angstroms.